
2SD1419

Silicon NPN Epitaxial

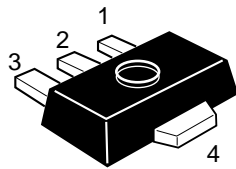
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Application

- Low frequency power amplifier
- Complementary pair with 2SB1026

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

2SD1419

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated	Unit
Collector to base voltage	V _{CBO}	120	V
Collector to emitter voltage	V _{CEO}	100	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	I _C	1	A
Collector peak current	i _{C(peak)} ^{*1}	2	A
Collector power dissipation	P _C ^{*2}	1	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

- Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%
2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

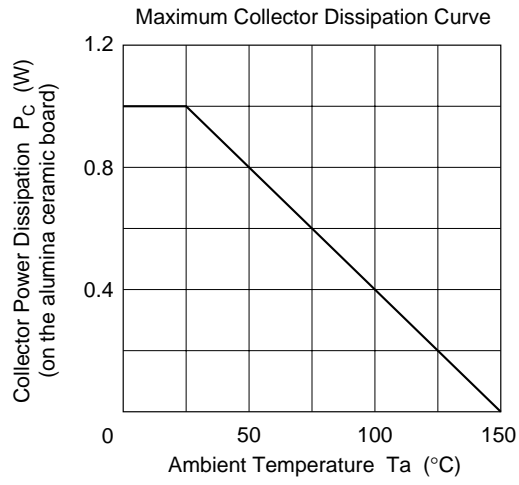
Electrical Characteristics (Ta = 25°C)

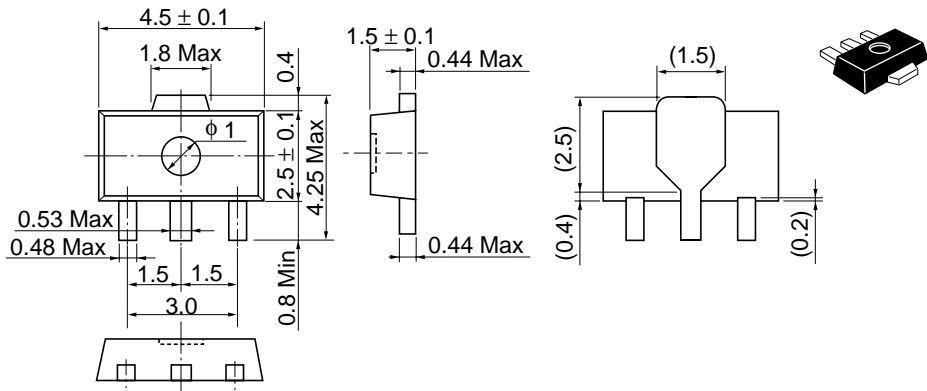
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	120	—	—	V	I _C = 10 μA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	100	—	—	V	I _C = 1 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	5	—	—	V	I _E = 10 μA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	10	μA	V _{CB} = 100 V, I _E = 0
DC current transfer ratio	h _{FE1} ^{*1}	60	—	200		V _{CE} = 5 V, I _C = 150 mA ^{*2}
	h _{FE2}	30	—	—		V _{CE} = 5 V, I _C = 500 mA ^{*2}
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	1	V	I _C = 500 mA, I _B = 50 mA ^{*2}
Base to emitter voltage	V _{BE}	—	—	1.5	V	V _{CE} = 5 V, I _C = 150 mA ^{*2}
Gain bandwidth product	f _T	—	140	—	MHz	V _{CE} = 5 V, I _C = 150 mA ^{*2}
Collector output capacitance	C _{ob}	—	12	—	pF	V _{CB} = 10 V, I _E = 0, f = 1 MHz

- Notes: 1. The 2SD1419 is grouped by h_{FE1} as follows.
2. Pulse test

Mark	DD	DE
h _{FE1}	60 to 120	100 to 200

See characteristic curves of 2SD1418.





Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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